Pentacene organic diode with very low turn on voltage for RF energy harvesting applications

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Avec le soutien du Fonds européen de développement régional Met steun van het Europees Fonds voor Regionale Ontwikkeling Khaoula ferchichi^{1,2} David Guerin¹, Ramzi Bourguiga², Kamal Lmimouni¹

¹IEMN Institut d'électronique de microélectronique et nanotechnologie, Avenue Poincaré, 59652 Villeneuve d'Ascq, France. ²Laboratoire Physique des Matériaux, Structures et Propriétés Groupe Physique des Composants et Dispositifs Nanométriques, Facultés des sciences de Bizerte, 7021 Jarzouna-Bizerte, Tunisie

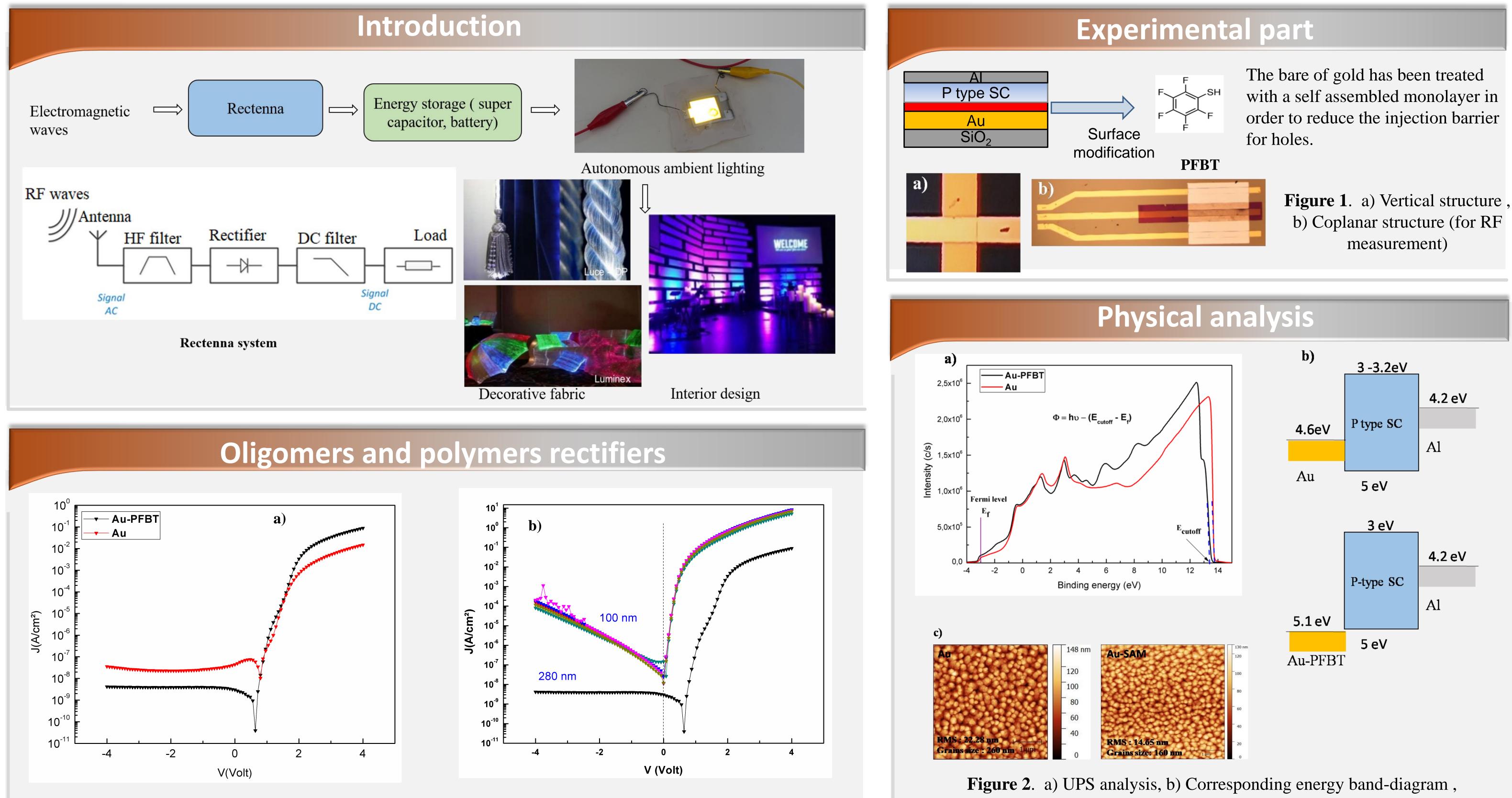
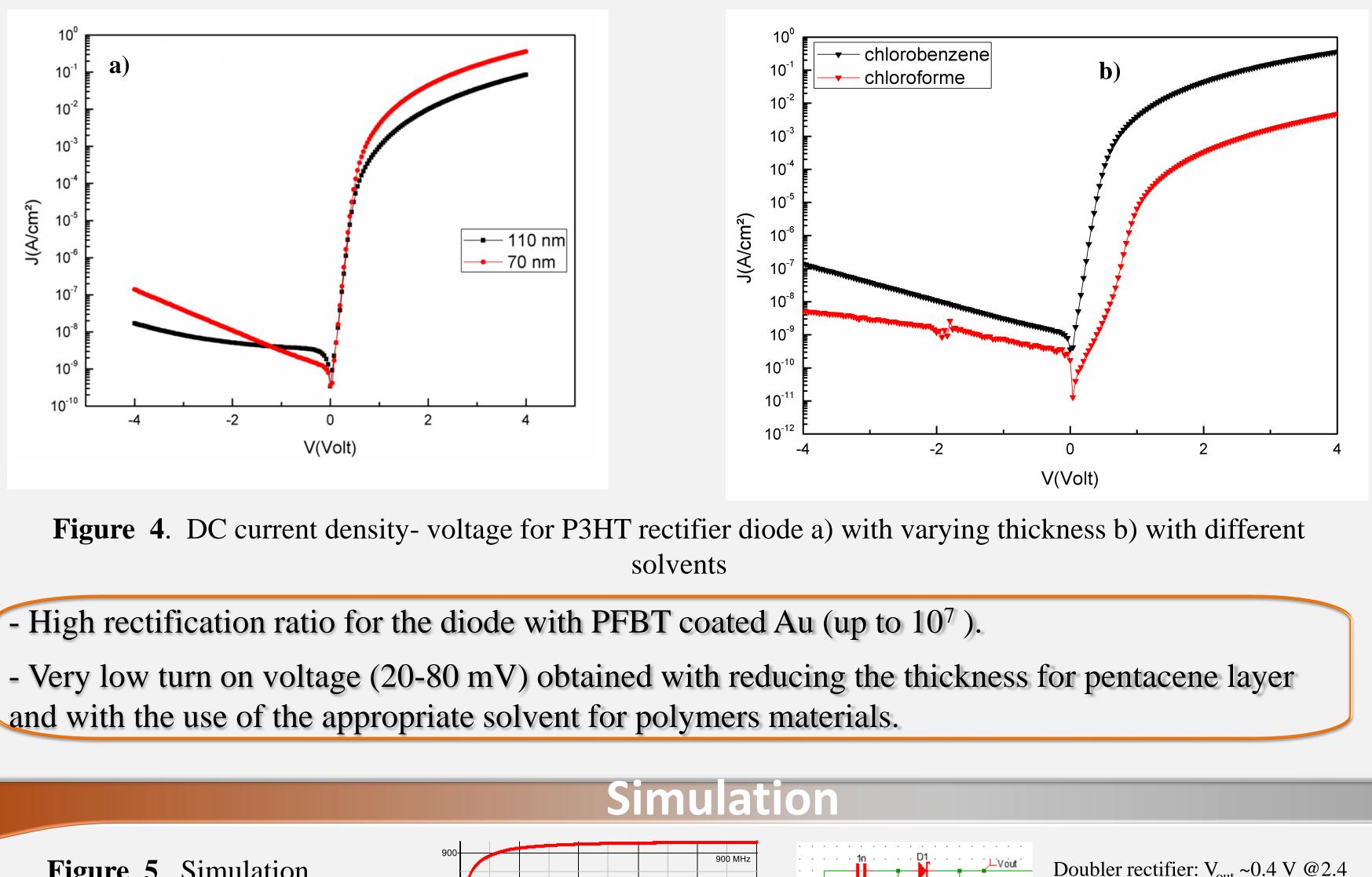


Figure 3. DC current density- voltage for pentacene rectifier : a) with and without surface modification , b) With varying thickness of pentacene layer.

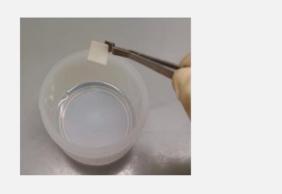
-Low injection barrier for holes with treated gold (0.1 eV).

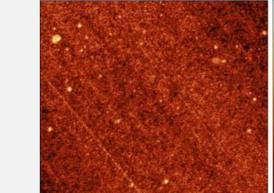


- Low roughness for SAM treated pentacene (~14 nm)

c) AFM analysis

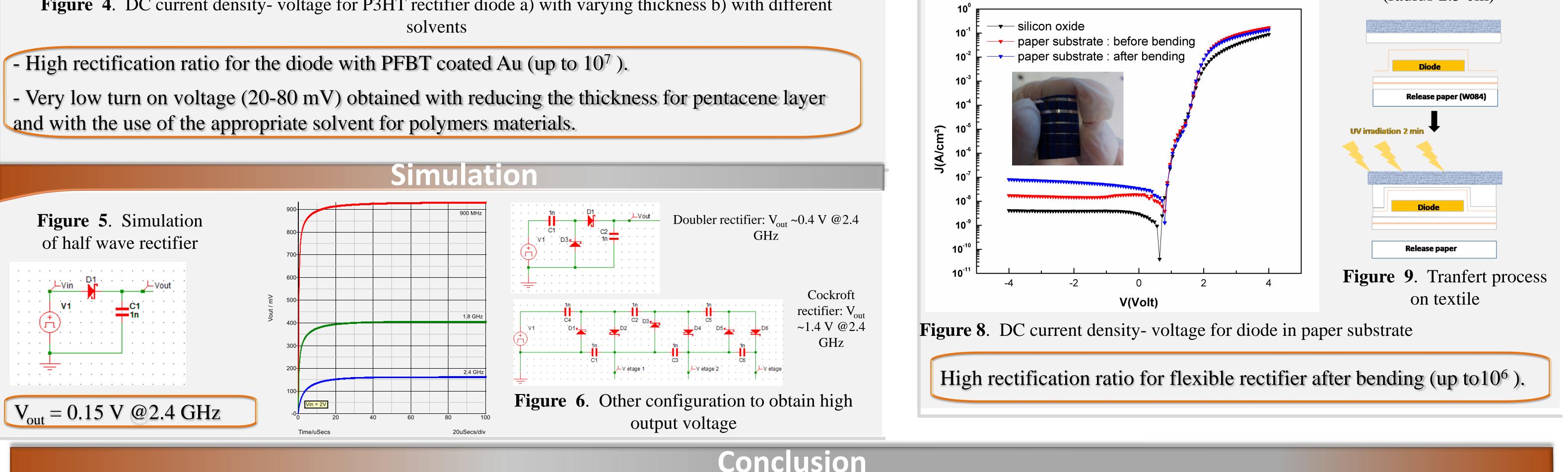
Pentacene flexible rectifier for smart textile





Paper stability in solvent (ethanol)

Low roughness of paper (1.4 nm)



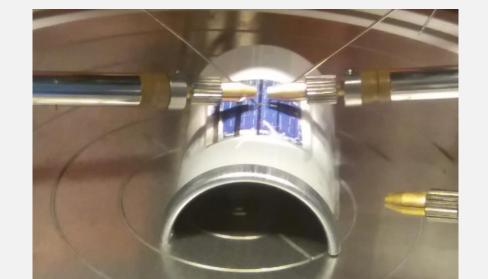
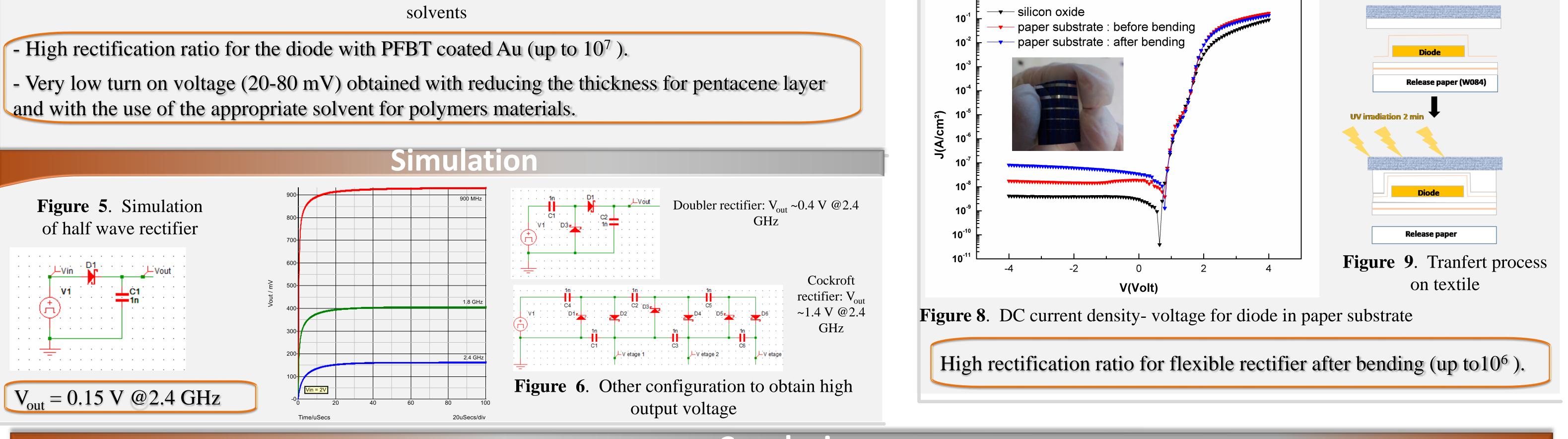


Figure 7. Bending test (radius 2.5 cm)



In this study, diodes with oligomers and polymers have been fabricated and characterized. With controlling different parameters of active layer deposition (thickness, polymer solvents) and by using SAM modification of gold electrode, we demonstrate that organic rectifiers with a high rectification ratio and very low turn on voltage can be obtained. Flexible pentacene diodes also show a high stability even after bending. The simulation shows that we can achieve a frequency response of about 0.15 at 2.4 GHz with a simple diode rectifier design. These components are suitable for RF energy harvesting.

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